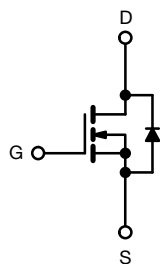
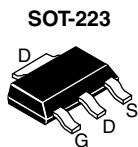


## Power MOSFET



N-Channel MOSFET

Marking code: FD

| PRODUCT SUMMARY           |                        |     |
|---------------------------|------------------------|-----|
| $V_{DS}$ (V)              | 250                    |     |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10\text{ V}$ | 2.0 |
| $Q_g$ (Max.) (nC)         | 8.2                    |     |
| $Q_{gs}$ (nC)             | 1.8                    |     |
| $Q_{gd}$ (nC)             | 4.5                    |     |
| Configuration             | Single                 |     |

| ORDERING INFORMATION            |                                  |
|---------------------------------|----------------------------------|
| Package                         | SOT-223                          |
| Lead (Pb)-free and halogen-free | SiHFL214TR-GE3 <sup>a</sup>      |
|                                 | IRFL214TRPbF-BE3 <sup>a, b</sup> |
| Lead (Pb)-free                  | IRFL214TRPbF <sup>a</sup>        |

### Notes

- a. See device orientation  
b. “-BE3” denotes alternate manufacturing location

| ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted) |                         |                         |                                   |             |      |
|---------------------------------------------------------------------------|-------------------------|-------------------------|-----------------------------------|-------------|------|
| PARAMETER                                                                 |                         |                         | SYMBOL                            | LIMIT       | UNIT |
| Drain-source voltage                                                      |                         |                         | V <sub>DS</sub>                   | 250         | V    |
| Gate-source voltage                                                       |                         |                         | V <sub>GS</sub>                   | ± 20        |      |
| Continuous drain current                                                  | V <sub>GS</sub> at 10 V | T <sub>C</sub> = 25 °C  | I <sub>D</sub>                    | 0.79        | A    |
|                                                                           |                         | T <sub>C</sub> = 100 °C |                                   | 0.50        |      |
| Pulsed drain current <sup>a</sup>                                         |                         |                         | I <sub>DM</sub>                   | 6.3         |      |
| Linear derating factor                                                    |                         |                         |                                   | 0.025       | W/°C |
| Linear derating factor (PCB mount) <sup>e</sup>                           |                         |                         |                                   | 0.017       |      |
| Single pulse avalanche energy <sup>b</sup>                                |                         |                         | E <sub>AS</sub>                   | 50          | mJ   |
| Avalanche current <sup>a</sup>                                            |                         |                         | I <sub>AR</sub>                   | 0.79        | A    |
| Repetitive avalanche energy <sup>a</sup>                                  |                         |                         | E <sub>AR</sub>                   | 0.31        | mJ   |
| Maximum power dissipation                                                 | T <sub>C</sub> = 25 °C  |                         | P <sub>D</sub>                    | 3.1         | W    |
| Maximum power dissipation (PCB mount) <sup>e</sup>                        | T <sub>A</sub> = 25 °C  |                         |                                   | 2.0         |      |
| Peak diode recovery dv/dt <sup>c</sup>                                    |                         |                         | dV/dt                             | 4.8         | V/ns |
| Operating junction and storage temperature range                          |                         |                         | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 | °C   |
| Soldering recommendations (peak temperature) <sup>d</sup>                 | For 10 s                |                         |                                   | 300         |      |

### Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)  
b.  $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 128\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 0.79\text{ A}$  (see fig. 12)  
c.  $I_{SD} \leq 2.7\text{ A}$ ,  $dI/dt \leq 65\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$   
d. 1.6 mm from case  
e. When mounted on 1" square PCB (FR-4 or G-10 material)

### FEATURES

- Surface-mount
- Available in tape and reel
- Dynamic  $dV/dt$  rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SOT-223 package is designed for surface-mounting using vapor phase, infrared, or wave soldering techniques. Its unique package design allows for easy automatic pick-and-place as with other SOT or SOIC packages but has the added advantage of improved thermal performance due to an enlarged tab for heatsinking. Power dissipation of greater than 1.25 W is possible in a typical surface mount application.



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**THERMAL RESISTANCE RATINGS**

| PARAMETER                                            | SYMBOL     | MIN. | TYP. | MAX. | UNIT |
|------------------------------------------------------|------------|------|------|------|------|
| Maximum junction-to-ambient (PCB mount) <sup>a</sup> | $R_{thJA}$ | -    | -    | 60   | °C/W |
| Maximum junction-to-case (drain)                     | $R_{thJC}$ | -    | -    | 40   |      |

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material)

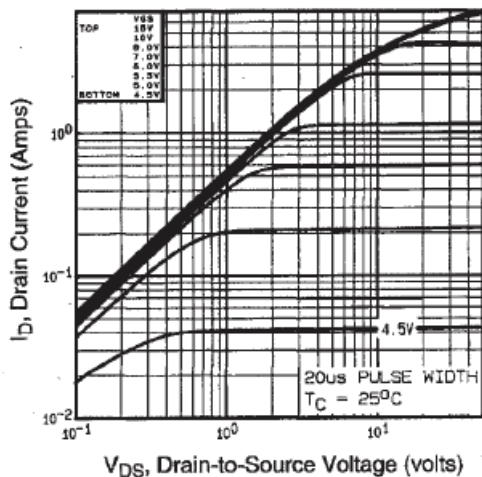
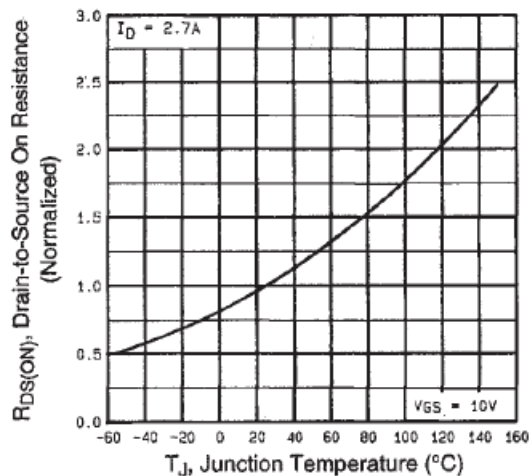
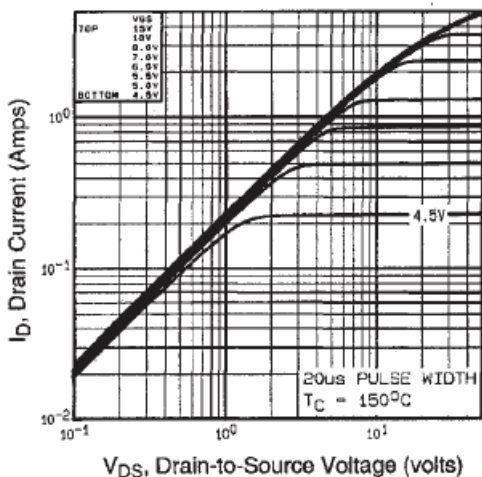
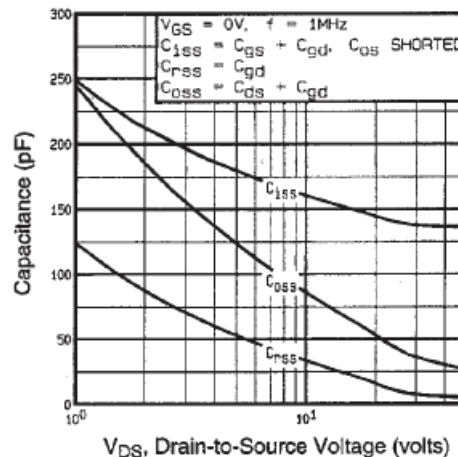
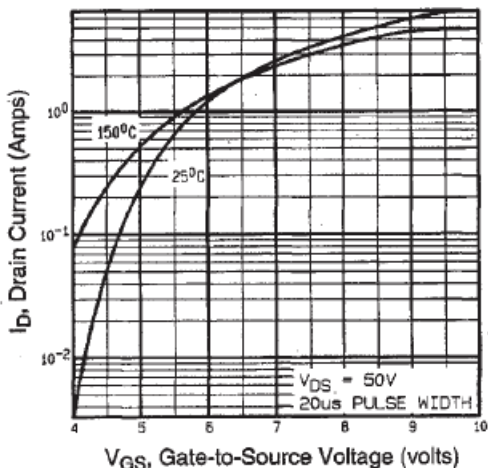
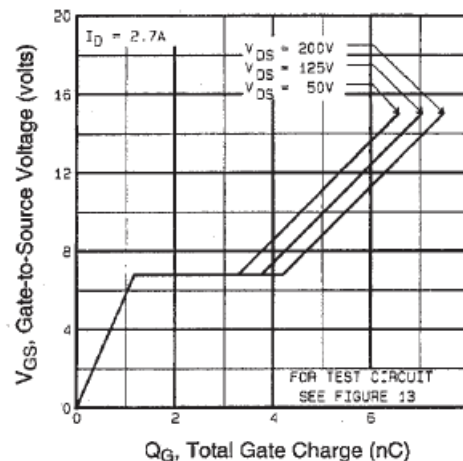
**SPECIFICATIONS** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

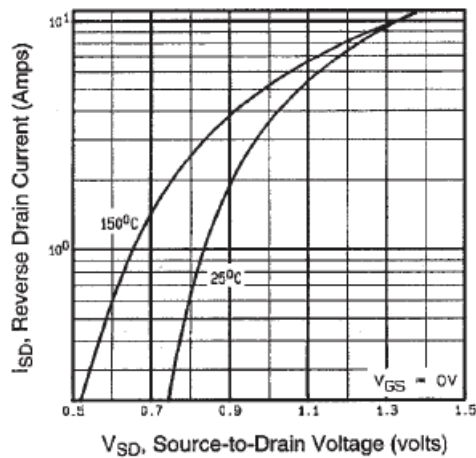
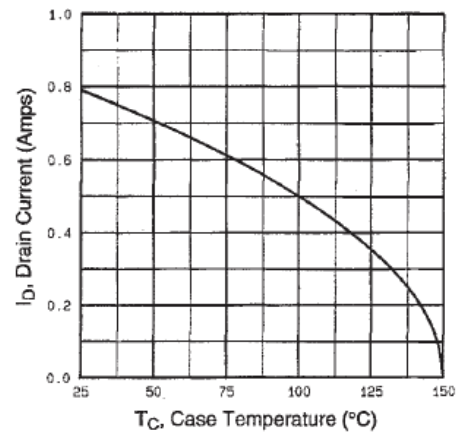
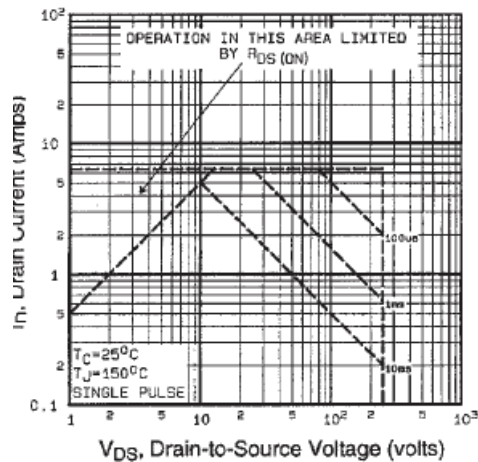
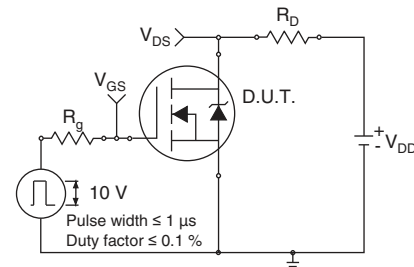
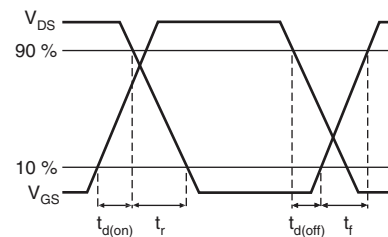
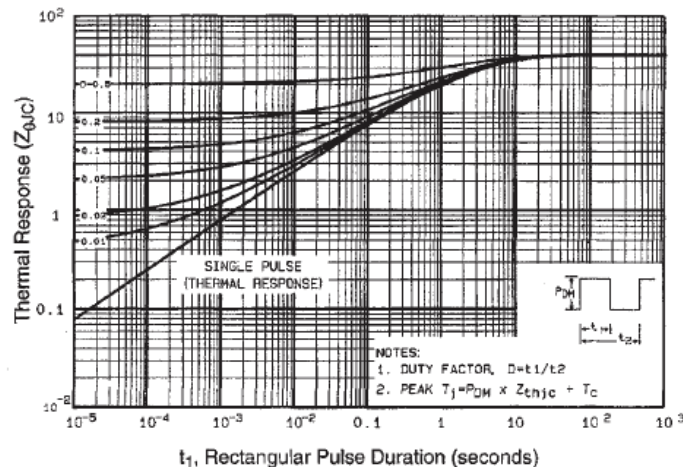
| PARAMETER                                 | SYMBOL                           | TEST CONDITIONS                                                                                                            |                                                                                    | MIN. | TYP. | MAX.  | UNIT |
|-------------------------------------------|----------------------------------|----------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------|------|------|-------|------|
| Static                                    |                                  |                                                                                                                            |                                                                                    |      |      |       |      |
| Drain-source breakdown voltage            | V <sub>DS</sub>                  | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                             |                                                                                    | 250  | -    | -     | V    |
| V <sub>DS</sub> temperature coefficient   | ΔV <sub>DS</sub> /T <sub>J</sub> | Reference to 25 °C, I <sub>D</sub> = 1 mA                                                                                  |                                                                                    | -    | 0.39 | -     | V/°C |
| Gate-source threshold voltage             | V <sub>GS(th)</sub>              | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                                |                                                                                    | 2.0  | -    | 4.0   | V    |
| Gate-source leakage                       | I <sub>GSS</sub>                 | V <sub>GS</sub> = ± 20 V                                                                                                   |                                                                                    | -    | -    | ± 100 | nA   |
| Zero gate voltage drain current           | I <sub>DSS</sub>                 | V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V                                                                             |                                                                                    | -    | -    | 25    | μA   |
|                                           |                                  | V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C                                                    |                                                                                    | -    | -    | 250   |      |
| Drain-source on-state resistance          | R <sub>DS(on)</sub>              | V <sub>GS</sub> = 10 V                                                                                                     | I <sub>D</sub> = 0.47 A <sup>b</sup>                                               | -    | -    | 2.0   | Ω    |
| Forward transconductance                  | g <sub>fs</sub>                  | V <sub>DS</sub> = 50 V, I <sub>D</sub> = 0.47 A                                                                            |                                                                                    | 0.50 | -    | -     | S    |
| Dynamic                                   |                                  |                                                                                                                            |                                                                                    |      |      |       |      |
| Input capacitance                         | C <sub>iss</sub>                 | V <sub>GS</sub> = 0 V,<br>V <sub>DS</sub> = 25 V,<br>f = 1.0 MHz, see fig. 5                                               |                                                                                    | -    | 140  | -     | pF   |
| Output capacitance                        | C <sub>oss</sub>                 |                                                                                                                            |                                                                                    | -    | 42   | -     |      |
| Reverse transfer capacitance              | C <sub>rss</sub>                 |                                                                                                                            |                                                                                    | -    | 9.6  | -     |      |
| Total gate charge                         | Q <sub>g</sub>                   | V <sub>GS</sub> = 10 V                                                                                                     | I <sub>D</sub> = 2.7 A, V <sub>DS</sub> = 200 V,<br>see fig. 6 and 13 <sup>b</sup> | -    | -    | 8.2   | nC   |
| Gate-source charge                        | Q <sub>gs</sub>                  |                                                                                                                            |                                                                                    | -    | -    | 1.8   |      |
| Gate-drain charge                         | Q <sub>gd</sub>                  |                                                                                                                            |                                                                                    | -    | -    | 4.5   |      |
| Turn-on delay time                        | t <sub>d(on)</sub>               | V <sub>DD</sub> = 125 V, I <sub>D</sub> = 2.7 A,<br>R <sub>g</sub> = 24 Ω, R <sub>D</sub> = 45 Ω, see fig. 10 <sup>b</sup> |                                                                                    | -    | 7.0  | -     | ns   |
| Rise time                                 | t <sub>r</sub>                   |                                                                                                                            |                                                                                    | -    | 7.6  | -     |      |
| Turn-off delay time                       | t <sub>d(off)</sub>              |                                                                                                                            |                                                                                    | -    | 16   | -     |      |
| Fall time                                 | t <sub>f</sub>                   |                                                                                                                            |                                                                                    | -    | 7.0  | -     |      |
| Internal drain inductance                 | L <sub>D</sub>                   | Between lead,<br>6 mm (0.25") from<br>package and center of<br>die contact                                                 |                                                                                    | -    | 4.0  | -     | nH   |
| Internal source inductance                | L <sub>S</sub>                   |                                                                                                                            |                                                                                    | -    | 6.0  | -     |      |
| Drain-Source Body Diode Characteristics   |                                  |                                                                                                                            |                                                                                    |      |      |       |      |
| Continuous source-drain diode current     | I <sub>S</sub>                   | MOSFET symbol<br>showing the<br>integral reverse<br>p - n junction diode                                                   |                                                                                    | -    | -    | 0.79  | A    |
| Pulsed diode forward current <sup>a</sup> | I <sub>SM</sub>                  |                                                                                                                            |                                                                                    | -    | -    | 6.3   |      |
| Body diode voltage                        | V <sub>SD</sub>                  | T <sub>J</sub> = 25 °C, I <sub>S</sub> = 0.79 A, V <sub>GS</sub> = 0 V <sup>b</sup>                                        |                                                                                    | -    | -    | 2.0   | V    |
| Body diode reverse recovery time          | t <sub>rr</sub>                  | T <sub>J</sub> = 25 °C, I <sub>F</sub> = 2.7 A, dI/dt = 100 A/μs <sup>b</sup>                                              |                                                                                    | -    | 190  | 390   | ns   |
| Body diode reverse recovery charge        | Q <sub>rr</sub>                  |                                                                                                                            |                                                                                    | -    | 0.64 | 1.3   | μC   |
| Forward turn-on time                      | t <sub>on</sub>                  | Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )                          |                                                                                    |      |      |       |      |

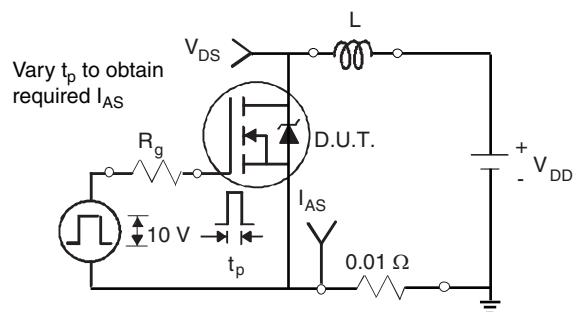
**Notes**

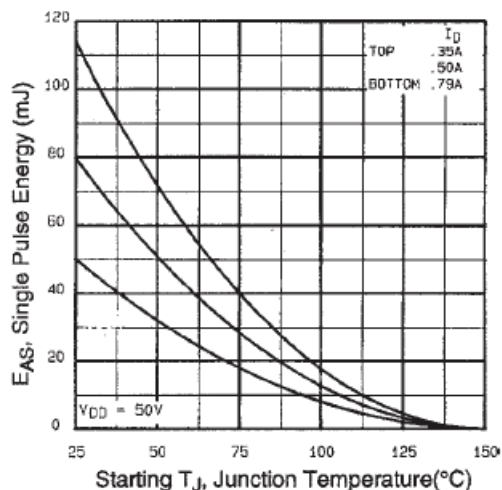
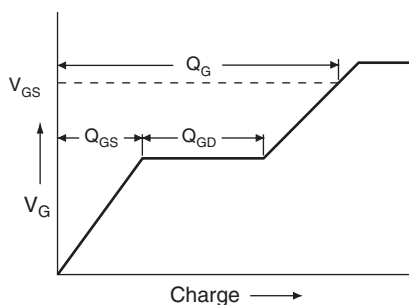
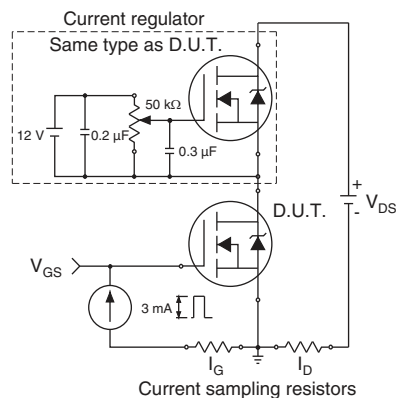
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

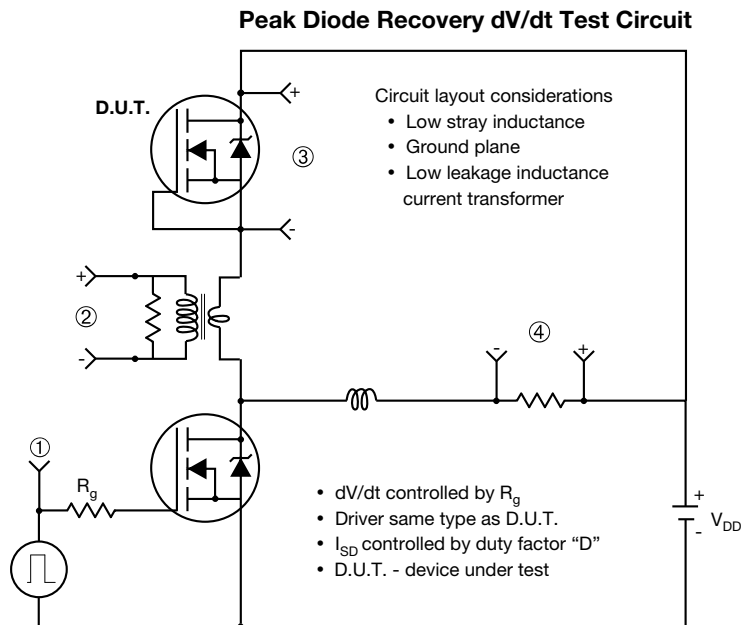
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**


**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

**Fig. 9 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Maximum Safe Operating Area**

**Fig. 10a - Switching Time Test Circuit**

**Fig. 10b - Switching Time Waveforms**

**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**


**Fig. 12a - Unclamped Inductive Test Circuit**

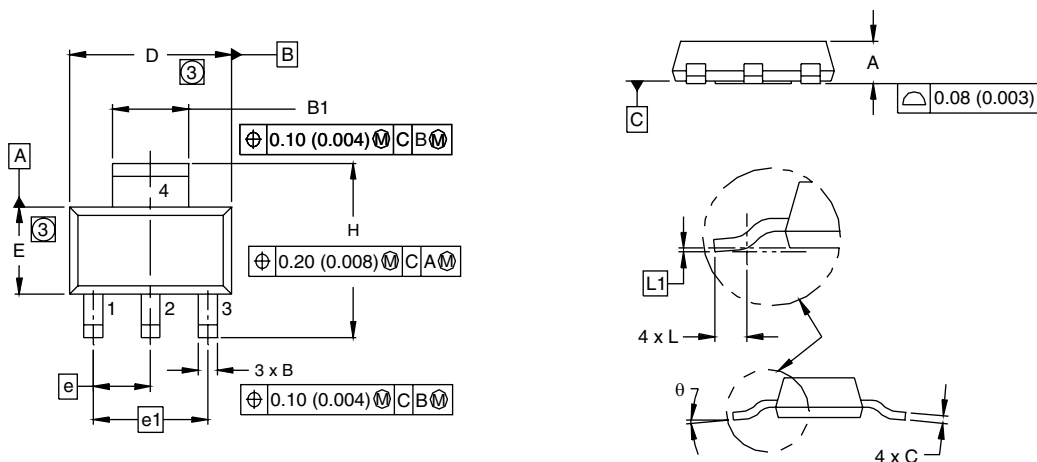
**Fig. 12b - Unclamped Inductive Waveforms**

**Fig. 12c - Maximum Avalanche Energy vs. Drain Current**

**Fig. 13a - Basic Gate Charge Waveform**

**Fig. 13b - Gate Charge Test Circuit**



**Fig.14 - For N-Channel**

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## SOT-223 (HIGH VOLTAGE)



| DIM.                                        | MILLIMETERS |      | INCHES     |       |
|---------------------------------------------|-------------|------|------------|-------|
|                                             | MIN.        | MAX. | MIN.       | MAX.  |
| A                                           | 1.55        | 1.80 | 0.061      | 0.071 |
| B                                           | 0.65        | 0.85 | 0.026      | 0.033 |
| B1                                          | 2.95        | 3.15 | 0.116      | 0.124 |
| C                                           | 0.25        | 0.35 | 0.010      | 0.014 |
| D                                           | 6.30        | 6.70 | 0.248      | 0.264 |
| E                                           | 3.30        | 3.70 | 0.130      | 0.146 |
| e                                           | 2.30 BSC    |      | 0.0905 BSC |       |
| e1                                          | 4.60 BSC    |      | 0.181 BSC  |       |
| H                                           | 6.71        | 7.29 | 0.264      | 0.287 |
| L                                           | 0.91        | -    | 0.036      | -     |
| L1                                          | 0.061 BSC   |      | 0.0024 BSC |       |
| θ                                           | -           | 10°  | -          | 10°   |
| ECN: S-82109-Rev. A, 15-Sep-08<br>DWG: 5969 |             |      |            |       |

### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension do not include mold flash.
4. Outline conforms to JEDEC outline TO-261AA.



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